TOSHIBA Photo-interrupter Infrared LED+Phototransistor

# **TLP844**

## Still Camera and Digital Still Camera

#### Video Camera

### Personal Equipment and Small-sized OA Equipment

The TLP844 is photointerrupter which consists of a GaAs infrared LED and an Si phototransistor.

It is an ultra compact package and has a wide gap width.

• Ultra compact package:  $4 \times 2.6 \times 2.9$ mm

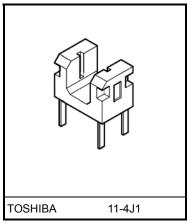
• Gap width: 2mm

• High resolution: Slit width = 0.3 mm

• High current transfer ratio: IC/IF = 3.5% (min)

Material of the package: Polybutylene terephthalate (UL94V-0)

• Lead-free product



Weight: 0.037 g (typ.)

## Maximum Ratings (Ta = 25°C)

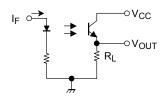
Characteristics		Symbol	Rating	Unit	
LED	Forward current	IF	30	mA	
	Forward current derating (Ta>25°C)	ΔI <sub>F</sub> /°C	-0.33	mA/°C	
	Reverse voltage	$V_{R}$	5	V	
Detector	Collector-emitter voltage	V <sub>CEO</sub>	35	V	
	Emitter-collector voltage	V <sub>ECO</sub>	5	٧	
	Collector power dissipation	PC	75	mW	
	Collector power dissipation derating (Ta>25°C)	ΔP <sub>C</sub> /°C	-1	mW/°C	
	Collector current	IC	50	mA	
Operating temperature range		T <sub>opr</sub>	-30 to 85	°C	
Storage temperature range		T <sub>stg</sub>	-40 to 100	°C	
Sold	lering temperature (5s) (Note 1)	T <sub>sol</sub>	260	°C	

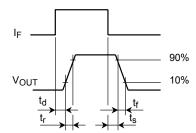
Note 1: At least 1mm from body

## Optical and Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test conditions	Min	Тур.	Max	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.10	1.23	1.40	V
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μА
	Peak emission wavelength	λР	I <sub>F</sub> = 10 mA	_	940	_	nm
Detector	Dark current	I <sub>D</sub> (I <sub>CEO</sub> )	V <sub>CE</sub> = 24 V, I <sub>F</sub> = 0	_	_	0.1	μА
	Peak sensitivity wavelength	λР	_	_	820	_	nm
Coupled	Current transfer ratio	I <sub>C</sub> /I <sub>F</sub>	V <sub>CE</sub> = 2 V, I <sub>F</sub> = 5 mA	3.5	_	35	%
	Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 0.175 mA	_	0.1	0.4	V
	Rise time	t <sub>r</sub>	$V_{CC} = 5 \text{ V}, I_{C} = 1 \text{ mA}$	_	15	50	0
	Fall time	t <sub>f</sub>	$R_L = 1k \Omega$ (Note 2)		15	50	μS

Note 2: Switching time measurement circuit and waveform



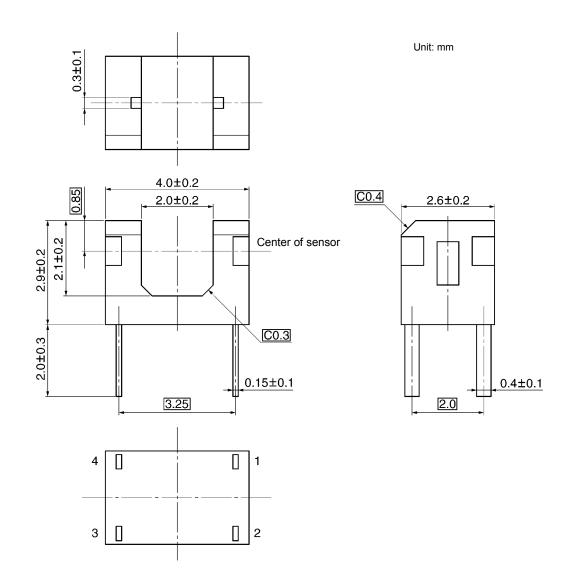


#### **Precautions**

- When removing flux with chemicals after soldering, clean only the leads on the soldering side; do not dip the whole package for cleaning.
  - Chemicals remaining on an LED or photo transistor light emitter or receiver, if any, would have a bad influence to the optical characteristics and it may severely lower the conversion efficiency.
- Protect the device from ambient light interference. If it gets strong ambient light (sunlight of high illumination, incandescent light with many infrared light ingredients, etc.) directly, it may cause malfunction. Please thoroughly evaluate the equipment in which the device is used.
- Care must be taken in relation to the environment in which the device is to be installed. Oil or chemicals
  may cause the package to melt or crack.
- The device should be mounted on an unwarped surface.
- Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time. The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1:1.

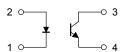
$$\frac{\mathrm{IC/IF}\;(\mathrm{t})}{\mathrm{IC/IF}\;(\mathrm{0})} = \frac{\mathrm{P_{0}}\;(\mathrm{t})}{\mathrm{P_{0}}\;(\mathrm{0})}$$

# Package Dimensions: TOSHIBA 11-4J1

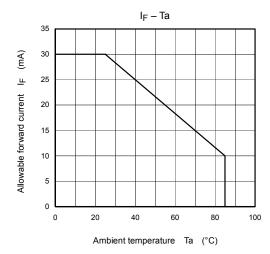


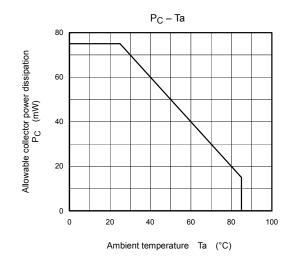
Weight: 0.037 g (typ.)

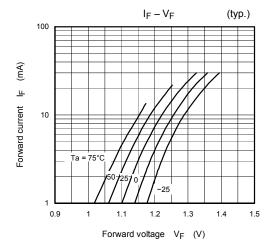
# **Pin Connection**

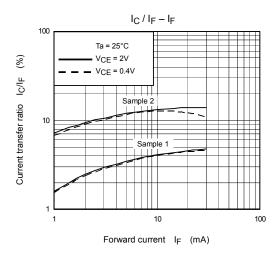


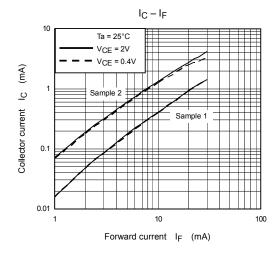
- 1: Cathode
- 2: Anode
- 3: Collector
- 4: Emitter

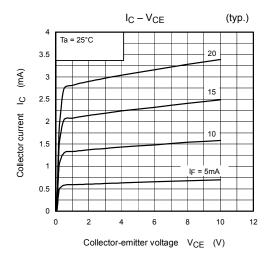


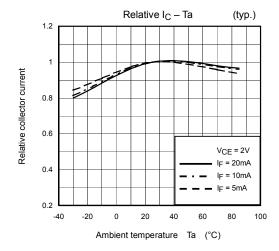


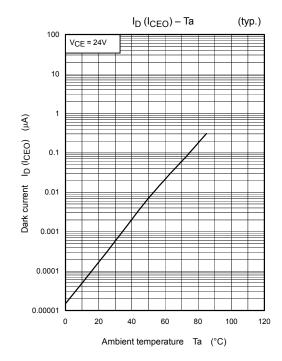


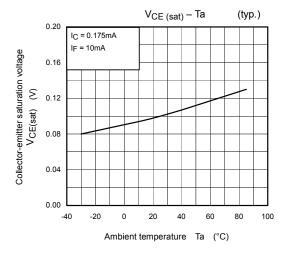


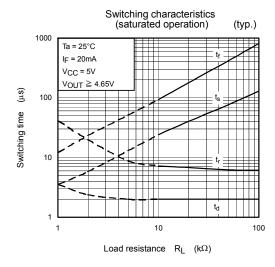


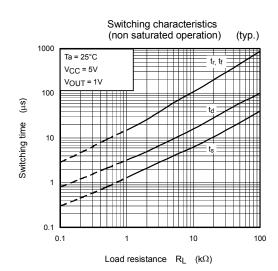


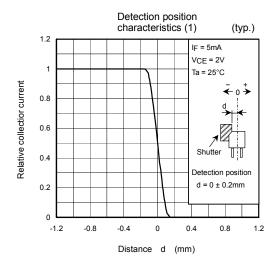


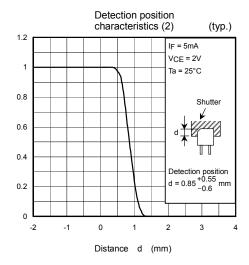






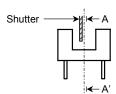


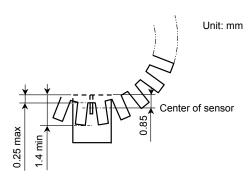




# **Relative Positioning of Shutter and Device**

For normal operation, position the shutter and the device as shown in the figure below. By considering the device's detection direction characteristic and switching time, determine the shutter slit width and pitch.





Cross section between A and A'

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